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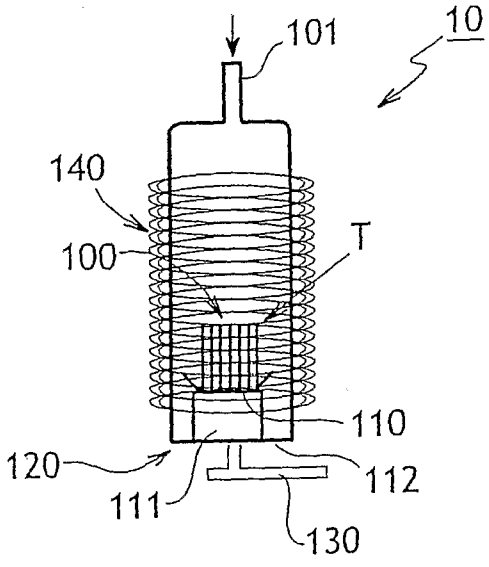
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(54) Title: METHOD OF DETACHING A SEMICONDUCTOR LAYER




(57) Abstract: The invention relates to a method of detachment of a layer from a wafer of material chosen from semiconductor materials, the method comprising the steps consisting of: creating an embrittlement zone in the thickness of the wafer, the said embrittlement zone defining the layer to be detached in the thickness of the wafer;subjecting the wafer to a treatment to perform detachment of the layer, at the level of the embrittlement zone; characterized in that during the creation of the embrittlement zone, a localized starting region of this zone is constituted, at the level of which the embrittlement zone locally has greater embrittlement, so that this starting region corresponds to a super-embrittled region of the embrittlement zone.

WO 2005/013355 A1